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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	38
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	52-LQFP
Supplier Device Package	52-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100jcdfa-v0

Table 1-1. List of Ordering Part Numbers

(4/12)

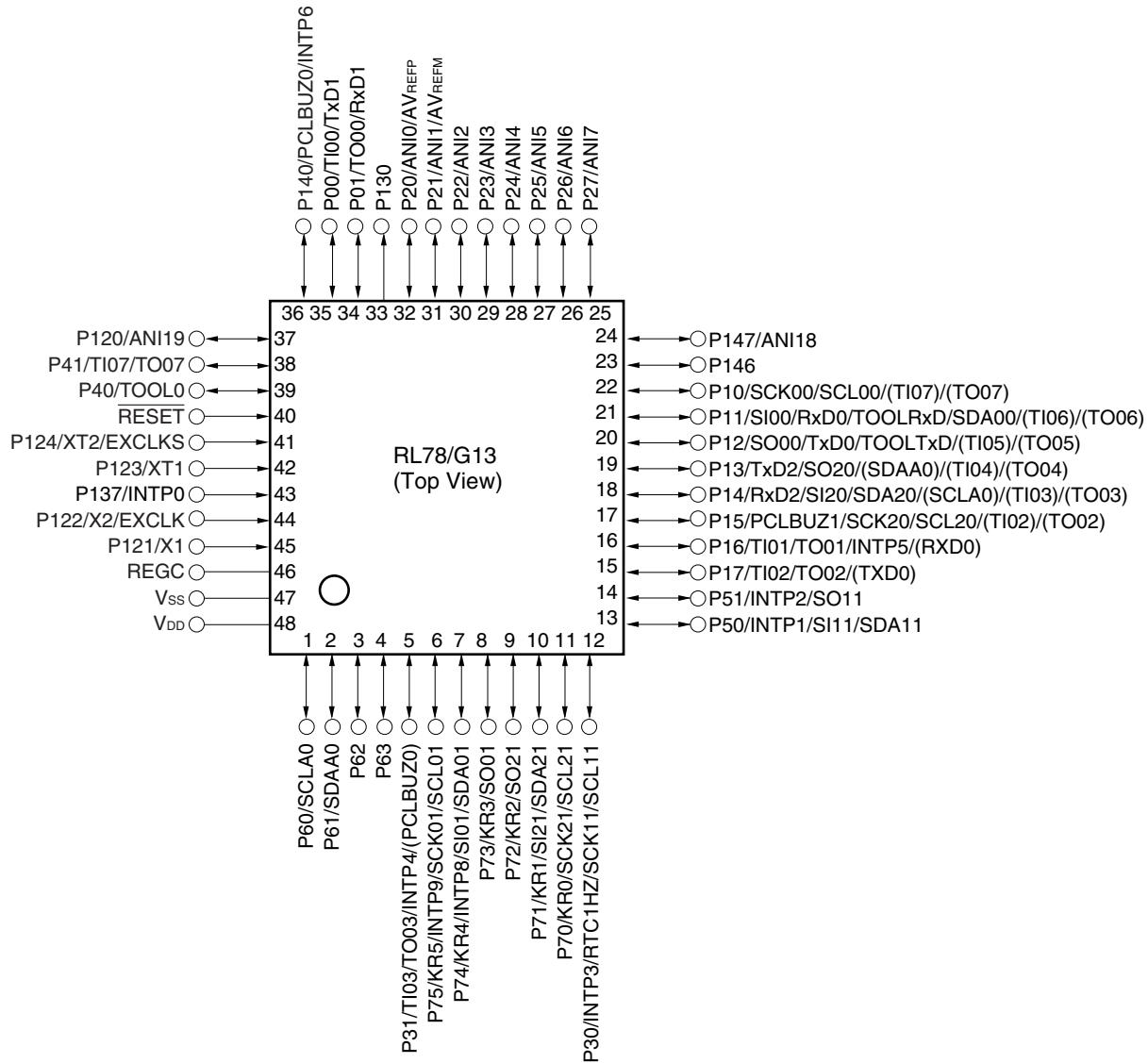
Pin count	Package	Data flash	Fields of Application <small>Note</small>	Ordering Part Number
44 pins	44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)	Mounted	A D G	R5F100FAAFP#V0, R5F100FC AFP#V0, R5F100FDAFP#V0, R5F100FEA FP#V0, R5F100FFA FP#V0, R5F100FGA FP#V0, R5F100FH A FP#V0, R5F100FJA FP#V0, R5F100FKA FP#V0, R5F100FLA FP#V0 R5F100FAAFP#X0, R5F100FC AFP#X0, R5F100FDAFP#X0, R5F100FEA FP#X0, R5F100FFA FP#X0, R5F100FGA FP#X0, R5F100FH A FP#X0, R5F100FJA FP#X0, R5F100FKA FP#X0, R5F100FLA FP#X0 R5F100FADFP#V0, R5F100FCDFP#V0, R5F100FDDFP#V0, R5F100FEDFP#V0, R5F100FFDFP#V0, R5F100FGDFP#V0, R5F100FHDFP#V0, R5F100FJDFP#V0, R5F100FKDFP#V0, R5F100FLDFP#V0 R5F100FADFP#X0, R5F100FCDFP#X0, R5F100FDDFP#X0, R5F100FEDFP#X0, R5F100FFDFP#X0, R5F100FGDFP#X0, R5F100FHDFP#X0, R5F100FJDFP#X0, R5F100FKDFP#X0, R5F100FLDFP#X0 R5F100FAGFP#V0, R5F100FC GFP#V0, R5F100FD GFP#V0, R5F100FEGFP#V0, R5F100FF GFP#V0, R5F100FG GFP#V0, R5F100FH GFP#V0, R5F100FJ GFP#V0 R5F100FAGFP#X0, R5F100FC GFP#X0, R5F100FD GFP#X0, R5F100FEGFP#X0, R5F100FF GFP#X0, R5F100FG GFP#X0, R5F100FH GFP#X0, R5F100FJ GFP#X0 Not mounted
			A D	R5F101FAAFP#V0, R5F101FC AFP#V0, R5F101FDAFP#V0, R5F101FEA FP#V0, R5F101FFA FP#V0, R5F101FGA FP#V0, R5F101FH A FP#V0, R5F101FJA FP#V0, R5F101FKA FP#V0, R5F101FLA FP#V0 R5F101FAAFP#X0, R5F101FC AFP#X0, R5F101FDAFP#X0, R5F101FEA FP#X0, R5F101FFA FP#X0, R5F101FGA FP#X0, R5F101FH A FP#X0, R5F101FJA FP#X0, R5F101FKA FP#X0, R5F101FLA FP#X0 R5F101FADFP#V0, R5F101FCDFP#V0, R5F101FDDFP#V0, R5F101FEDFP#V0, R5F101FFDFP#V0, R5F101FGDFP#V0, R5F101FHDFP#V0, R5F101FJDFP#V0, R5F101FKDFP#V0, R5F101FLDFP#V0 R5F101FADFP#X0, R5F101FCDFP#X0, R5F101FDDFP#X0, R5F101FEDFP#X0, R5F101FFDFP#X0, R5F101FGDFP#X0, R5F101FHDFP#X0, R5F101FJDFP#X0, R5F101FKDFP#X0, R5F101FLDFP#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.9 48-pin products

- 48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)



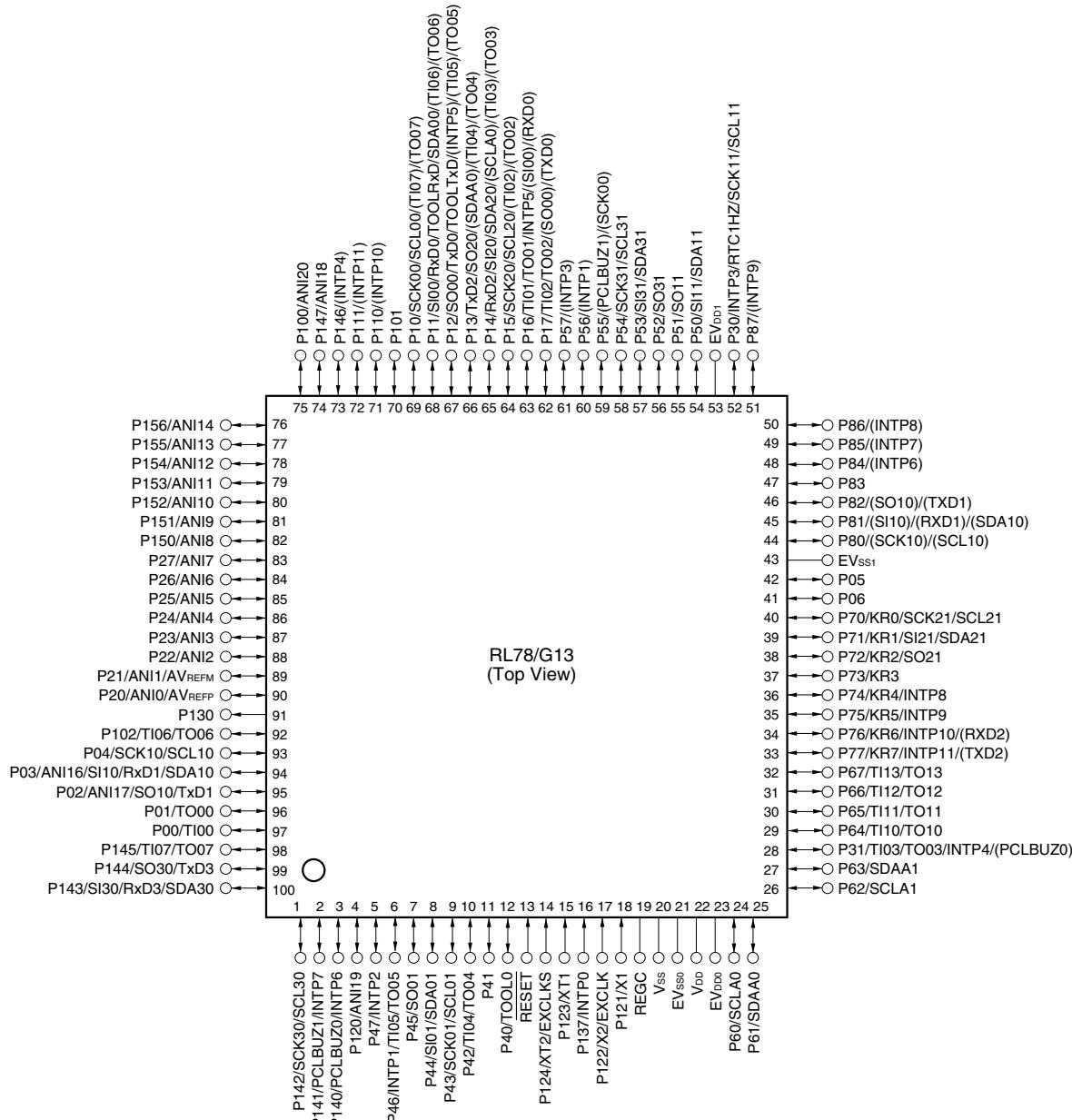
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.3.13 100-pin products

- 100-pin plastic LQFP (14 × 14 mm, 0.5 mm pitch)



2. Make V_{dd} pin the potential that is higher than EV_{dd0}, EV_{dd1} pins (EV_{dd0} = EV_{dd1}).
3. Connect the REGC pin to V_{ss} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{dd}, EV_{dd0} and EV_{dd1} pins and connect the V_{ss}, EV_{ss0} and EV_{ss1} pins to separate ground lines.
3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

[40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item	40-pin		44-pin		48-pin		52-pin		64-pin										
	R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx									
Code flash memory (KB)	16 to 192		16 to 512		16 to 512		32 to 512		32 to 512										
Data flash memory (KB)	4 to 8	—	4 to 8	—	4 to 8	—	4 to 8	—	4 to 8	—									
RAM (KB)	2 to 16 ^{Note1}		2 to 32 ^{Note1}		2 to 32 ^{Note1}		2 to 32 ^{Note1}		2 to 32 ^{Note1}										
Address space	1 MB																		
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)																	
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)																	
Subsystem clock	XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz																		
Low-speed on-chip oscillator	15 kHz (TYP.)																		
General-purpose registers	(8-bit register × 8) × 4 banks																		
Minimum instruction execution time	0.03125 μ s (High-speed on-chip oscillator: $f_{IH} = 32$ MHz operation) 0.05 μ s (High-speed system clock: $f_{MX} = 20$ MHz operation) 30.5 μ s (Subsystem clock: $f_{SUB} = 32.768$ kHz operation)																		
Instruction set	<ul style="list-style-type: none"> Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 																		
I/O port	Total	36	40	44	48	58													
	CMOS I/O	28 (N-ch O.D. I/O [V_{DD} withstand voltage]: 10)	31 (N-ch O.D. I/O [V_{DD} withstand voltage]: 10)	34 (N-ch O.D. I/O [V_{DD} withstand voltage]: 11)	38 (N-ch O.D. I/O [V_{DD} withstand voltage]: 13)	48 (N-ch O.D. I/O [V_{DD} withstand voltage]: 15)													
	CMOS input	5	5	5	5	5													
	CMOS output	—	—	1	1	1													
	N-ch O.D. I/O (withstand voltage: 6 V)	3	4	4	4	4													
Timer	16-bit timer	8 channels																	
	Watchdog timer	1 channel																	
	Real-time clock (RTC)	1 channel																	
	12-bit interval timer (IT)	1 channel																	
	Timer output	4 channels (PWM outputs: 3 ^{Note2}), 8 channels (PWM outputs: 7 ^{Note2, Note3})	5 channels (PWM outputs: 4 ^{Note2}), 8 channels (PWM outputs: 7 ^{Note2, Note3})	8 channels (PWM outputs: 7 ^{Note2})															
	RTC output	1 channel • 1 Hz (subsystem clock: $f_{SUB} = 32.768$ kHz)																	

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = E to G, J, L): Start address FF300H

R5F100xE, R5F101xE (x = E to G, J, L): Start address FEF00H

R5F100xJ, R5F101xJ (x = F, G, J, L): Start address FAF00H

R5F100xL, R5F101xL (x = F, G, J, L): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

[80-pin, 100-pin, 128-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item	80-pin		100-pin		128-pin										
	R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx									
Code flash memory (KB)	96 to 512		96 to 512		192 to 512										
Data flash memory (KB)	8	–	8	–	8	–									
RAM (KB)	8 to 32 ^{Note 1}		8 to 32 ^{Note 1}		16 to 32 ^{Note 1}										
Address space	1 MB														
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)													
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)													
Subsystem clock	XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz														
Low-speed on-chip oscillator	15 kHz (TYP.)														
General-purpose register	(8-bit register × 8) × 4 banks														
Minimum instruction execution time	0.03125 μ s (High-speed on-chip oscillator: $f_{IH} = 32$ MHz operation)														
	0.05 μ s (High-speed system clock: $f_{MX} = 20$ MHz operation)														
	30.5 μ s (Subsystem clock: $f_{SUB} = 32.768$ kHz operation)														
Instruction set	<ul style="list-style-type: none"> • Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 														
I/O port	Total	74	92	120											
	CMOS I/O	64 (N-ch O.D. I/O [EV_{DD} withstand voltage]: 21)	82 (N-ch O.D. I/O [EV_{DD} withstand voltage]: 24)	110 (N-ch O.D. I/O [EV_{DD} withstand voltage]: 25)											
	CMOS input	5	5	5											
	CMOS output	1	1	1											
	N-ch O.D. I/O (withstand voltage: 6 V)	4	4	4											
Timer	16-bit timer	12 channels	12 channels	16 channels											
	Watchdog timer	1 channel	1 channel	1 channel											
	Real-time clock (RTC)	1 channel	1 channel	1 channel											
	12-bit interval timer (IT)	1 channel	1 channel	1 channel											
	Timer output	12 channels (PWM outputs: 10 ^{Note 2})	12 channels (PWM outputs: 10 ^{Note 2})	16 channels (PWM outputs: 14 ^{Note 2})											
	RTC output	1 channel • 1 Hz (subsystem clock: $f_{SUB} = 32.768$ kHz)													

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xJ, R5F101xJ (x = M, P): Start address FAF00H

R5F100xL, R5F101xL (x = M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

($T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$) (3/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer 0.8EV _{DD0}		EV _{DD0}	V
	V_{IH2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V \leq EV _{DD0} \leq 5.5 V	2.2		EV _{DD0}
			TTL input buffer 3.3 V \leq EV _{DD0} < 4.0 V	2.0		EV _{DD0}
			TTL input buffer 1.6 V \leq EV _{DD0} < 3.3 V	1.5		EV _{DD0}
	V_{IH3}	P20 to P27, P150 to P156	0.7V _{DD}		V _{DD}	V
	V_{IH4}	P60 to P63	0.7EV _{DD0}		6.0	V
	V_{IH5}	P121 to P124, P137, EXCLK, EXCLKS, RESET	0.8V _{DD}		V _{DD}	V
Input voltage, low	V_{IL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer 0		0.2EV _{DD0}	V
	V_{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V \leq EV _{DD0} \leq 5.5 V	0		0.8
			TTL input buffer 3.3 V \leq EV _{DD0} < 4.0 V	0		0.5
			TTL input buffer 1.6 V \leq EV _{DD0} < 3.3 V	0		0.32
	V_{IL3}	P20 to P27, P150 to P156	0		0.3V _{DD}	V
	V_{IL4}	P60 to P63	0		0.3EV _{DD0}	V
	V_{IL5}	P121 to P124, P137, EXCLK, EXCLKS, RESET	0		0.2V _{DD}	V

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

($T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$) (5/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit		
Input leakage current, high	I _{LIH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147		V _I = EV _{DD0}		1	μA		
	I _{LIH2}	P20 to P27, P137, P150 to P156, RESET		V _I = V _{DD}		1	μA		
	I _{LIH3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)		V _I = V _{DD}	In input port or external clock input	1	μA		
						10	μA		
Input leakage current, low	I _{LIL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147		V _I = EV _{SS0}		-1	μA		
	I _{LIL2}	P20 to P27, P137, P150 to P156, RESET		V _I = V _{SS}		-1	μA		
	I _{LIL3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)		V _I = V _{SS}	In input port or external clock input	-1	μA		
						-10	μA		
On-chip pll-up resistance	R _U	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147		V _I = EV _{SS0} , In input port		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- (2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

($T_A = -40$ to $+85^\circ\text{C}$, $2.7 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 2/f_{CLK}$	$4.0 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$	62.5		250		500		ns
			$2.7 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$	83.3		250		500		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	$4.0 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		$t_{KCY1}/2 - 7$		$t_{KCY1}/2 - 50$		$t_{KCY1}/2 - 50$		ns
		$2.7 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		$t_{KCY1}/2 - 10$		$t_{KCY1}/2 - 50$		$t_{KCY1}/2 - 50$		ns
Slp setup time (to SCKp \uparrow) <small>Note 1</small>	t_{SIK1}	$4.0 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		23		110		110		ns
		$2.7 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		33		110		110		ns
Slp hold time (from SCKp \uparrow) <small>Note 2</small>	t_{KSI1}	$2.7 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		10		10		10		ns
Delay time from SCKp \downarrow to SOp output <small>Note 3</small>	t_{KS01}	$C = 20 \text{ pF}$ <small>Note 4</small>			10		10		10	ns

- Notes**
- When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp \downarrow ” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp \downarrow ” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp \uparrow ” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. This value is valid only when CSI00’s peripheral I/O redirect function is not used.

- p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
g: PIM and POM numbers (g = 1)
3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

(2) I²C fast mode $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f _{SCL}	Fast mode: $f_{CLK} \geq 3.5 \text{ MHz}$	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	0	400	0	400	0	400	kHz
			1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	0	400	0	400	0	400	kHz
Setup time of restart condition	t _{SU:STA}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
Hold time ^{Note 1}	t _{HD:STA}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
Hold time when SCLA0 = "L"	t _{LOW}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		1.3		1.3		1.3		μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		1.3		1.3		1.3		μs
Hold time when SCLA0 = "H"	t _{HIGH}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
Data setup time (reception)	t _{SU:DAT}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		100		100		100		μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		100		100		100		μs
Data hold time (transmission) ^{Note 2}	t _{HD:DAT}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0	0.9	0	0.9	0	0.9	μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0	0.9	0	0.9	0	0.9	μs
Setup time of stop condition	t _{SU:STO}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
Bus-free time	t _{BUF}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		1.3		1.3		1.3		μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		1.3		1.3		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

<R> 2. The maximum value (MAX.) of t_{HD:DAT} is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: C_b = 320 pF, R_b = 1.1 k Ω

(2) When reference voltage (+) = $\text{AV}_{\text{REFP}}/\text{ANI}0$ ($\text{ADREFP}1 = 0$, $\text{ADREFP}0 = 1$), reference voltage (-) = $\text{AV}_{\text{REFM}}/\text{ANI}1$ ($\text{ADREFM} = 1$), target pin : ANI16 to ANI26

($T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$, $1.6 \text{ V} \leq \text{AV}_{\text{REFP}} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$, $\text{V}_{\text{ss}} = \text{EV}_{\text{ss}0} = \text{EV}_{\text{ss}1} = 0 \text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (-) = $\text{AV}_{\text{REFM}} = 0 \text{ V}$)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $\text{EV}_{\text{DD}0} = \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Notes 3, 4}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$		1.2	± 5.0	LSB
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 5}		1.2	± 8.5	LSB
Conversion time	t _{CONV}	10-bit resolution Target ANI pin : ANI16 to ANI26	3.6 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.125		39	μs
			2.7 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.1875		39	μs
			1.8 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
			1.6 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	57		95	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution $\text{EV}_{\text{DD}0} = \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Notes 3, 4}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			± 0.35	%FSR
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 5}			± 0.60	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution $\text{EV}_{\text{DD}0} = \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Notes 3, 4}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			± 0.35	%FSR
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 5}			± 0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $\text{EV}_{\text{DD}0} = \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Notes 3, 4}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			± 3.5	LSB
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 5}			± 6.0	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $\text{EV}_{\text{DD}0} = \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Notes 3, 4}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			± 2.0	LSB
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 5}			± 2.5	LSB
Analog input voltage	V _{AIN}	ANI16 to ANI26		0		AV_{REFP} and $\text{EV}_{\text{DD}0}$	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $\text{AV}_{\text{REFP}} < \text{V}_{\text{DD}}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$.

Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$.

4. When $\text{AV}_{\text{REFP}} < \text{EV}_{\text{DD}0} \leq \text{V}_{\text{DD}}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$.

Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$.

Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$.

5. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

- (3) When reference voltage (+) = V_{DD} ($\text{ADREFP1} = 0$, $\text{ADREFP0} = 0$), reference voltage (-) = V_{SS} ($\text{ADREFM} = 0$), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$, Reference voltage (+) = V_{DD} , Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$		1.2	± 7.0	LSB
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3		1.2	± 10.5	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	3.6 V $\leq V_{DD} \leq 5.5 \text{ V}$	2.125		39	μs
			2.7 V $\leq V_{DD} \leq 5.5 \text{ V}$	3.1875		39	μs
			1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$	17		39	μs
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$	57		95	μs
Conversion time	t _{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V $\leq V_{DD} \leq 5.5 \text{ V}$	2.375		39	μs
			2.7 V $\leq V_{DD} \leq 5.5 \text{ V}$	3.5625		39	μs
			2.4 V $\leq V_{DD} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 0.60	%FSR
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 0.85	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 0.60	%FSR
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 0.85	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 4.0	LSB
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 6.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 2.0	LSB
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 2.5	LSB
Analog input voltage	V _{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI26		0		EV_{DD0}	V
		Internal reference voltage (2.4 V $\leq V_{DD} \leq 5.5 \text{ V}$, HS (high-speed main) mode)		V_{BGR} ^{Note 4}			V
		Temperature sensor output voltage (2.4 V $\leq V_{DD} \leq 5.5 \text{ V}$, HS (high-speed main) mode)		V_{TMPS25} ^{Note 4}			V

- Notes**
- Excludes quantization error ($\pm 1/2$ LSB).
 - This value is indicated as a ratio (%FSR) to the full-scale value.
 - When the conversion time is set to 57 μs (min.) and 95 μs (max.).
 - Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

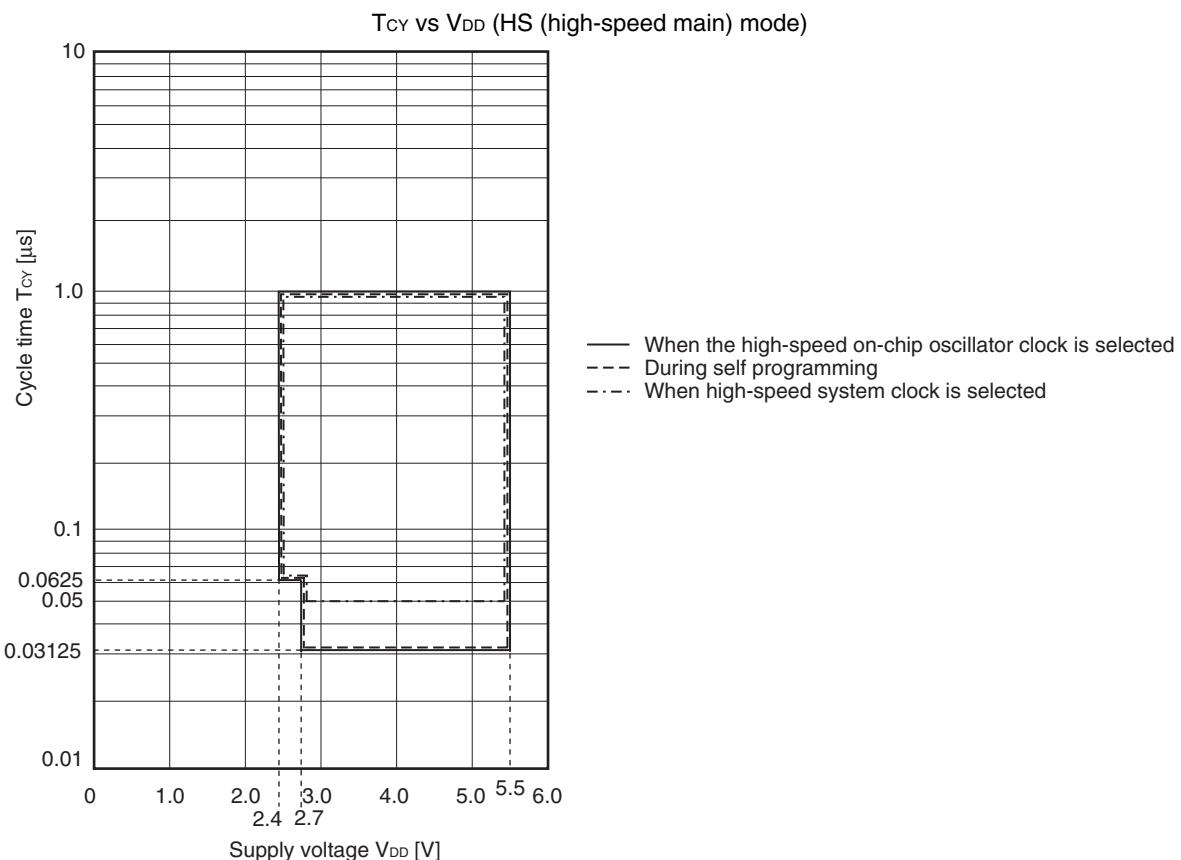
(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

 $(T_A = -40$ to $+105^\circ\text{C}$, $2.4 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$) (1/2)

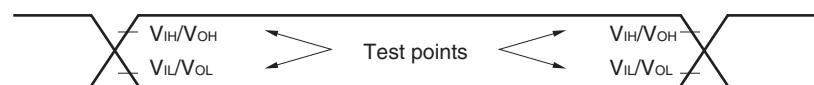
Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (high-speed main) mode Note 5	$f_{IH} = 32 \text{ MHz}$ ^{Note 3}	Basic operation	$V_{DD} = 5.0 \text{ V}$		2.3		mA
					Normal operation	$V_{DD} = 3.0 \text{ V}$		2.3		mA
					Normal operation	$V_{DD} = 5.0 \text{ V}$		5.2	9.2	mA
					Normal operation	$V_{DD} = 3.0 \text{ V}$		5.2	9.2	mA
				$f_{IH} = 24 \text{ MHz}$ ^{Note 3}	Normal operation	$V_{DD} = 5.0 \text{ V}$		4.1	7.0	mA
					Normal operation	$V_{DD} = 3.0 \text{ V}$		4.1	7.0	mA
		HS (high-speed main) mode Note 5	$f_{MX} = 20 \text{ MHz}$ ^{Note 2} , $V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		3.4	5.9		mA
				Normal operation	Resonator connection		3.6	6.0		mA
				Normal operation	Square wave input		3.4	5.9		mA
				Normal operation	Resonator connection		3.6	6.0		mA
			$f_{MX} = 10 \text{ MHz}$ ^{Note 2} , $V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		2.1	3.5		mA
				Normal operation	Resonator connection		2.1	3.5		mA
			$f_{MX} = 10 \text{ MHz}$ ^{Note 2} , $V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		2.1	3.5		mA
				Normal operation	Resonator connection		2.1	3.5		mA
		Subsystem clock operation	$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = -40^\circ\text{C}$	Normal operation	Square wave input		4.8	5.9		μA
				Normal operation	Resonator connection		4.9	6.0		μA
				Normal operation	Square wave input		4.9	5.9		μA
				Normal operation	Resonator connection		5.0	6.0		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +25^\circ\text{C}$	Normal operation	Square wave input		5.0	7.6		μA
				Normal operation	Resonator connection		5.1	7.7		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +50^\circ\text{C}$	Normal operation	Square wave input		5.2	9.3		μA
				Normal operation	Resonator connection		5.3	9.4		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +70^\circ\text{C}$	Normal operation	Square wave input		5.7	13.3		μA
				Normal operation	Resonator connection		5.8	13.4		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +85^\circ\text{C}$	Normal operation	Square wave input		10.0	46.0		μA
				Normal operation	Resonator connection		10.0	46.0		μA

(Notes and Remarks are listed on the next page.)

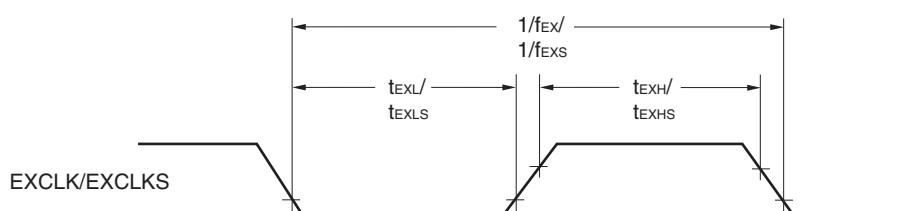
Minimum Instruction Execution Time during Main System Clock Operation

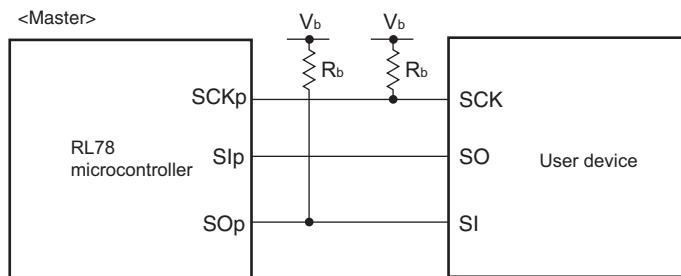


AC Timing Test Points



External System Clock Timing

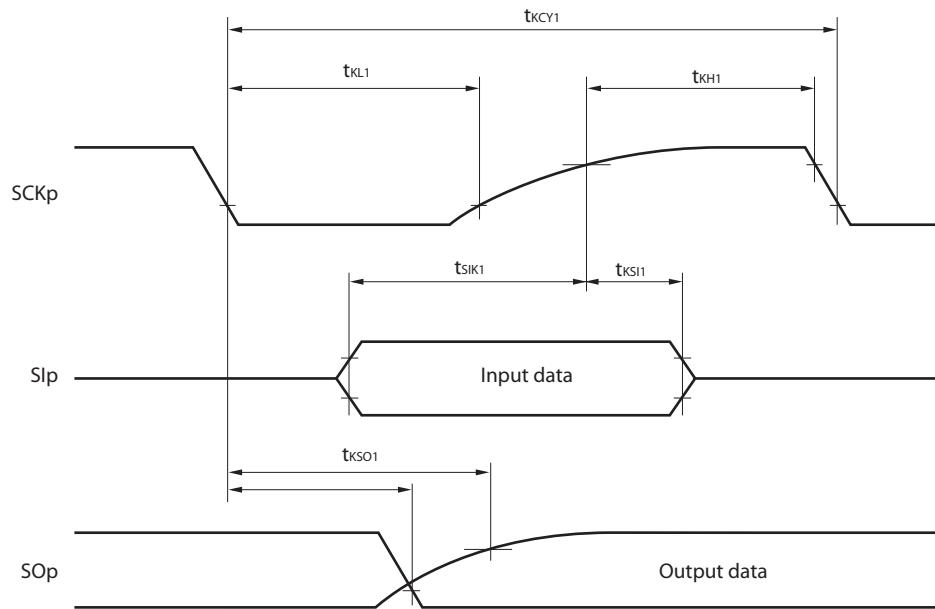


CSI mode connection diagram (during communication at different potential)

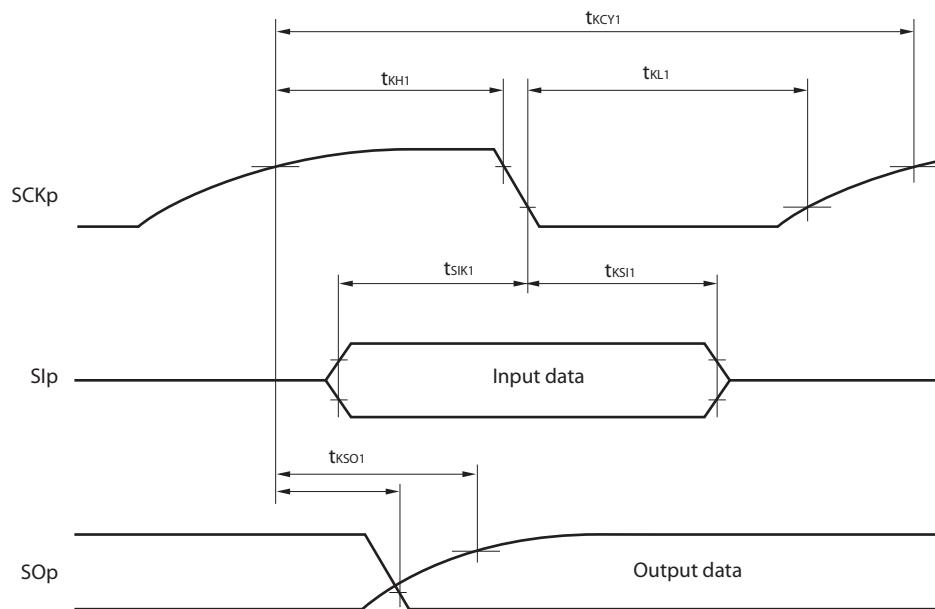
- Remarks**
1. $R_b[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, $C_b[F]$: Communication line (SCKp, SOp) load capacitance, $V_b[V]$: Communication line voltage
 2. p: CSI number ($p = 00, 01, 10, 20, 30, 31$), m: Unit number , n: Channel number ($mn = 00, 01, 02, 10, 12, 13$), g: PIM and POM number ($g = 0, 1, 4, 5, 8, 14$)
 3. fmck: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number ($mn = 00$))
 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.
Use other CSI for communication at different potential.

CSI mode serial transfer timing (master mode) (during communication at different potential)

(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

**CSI mode serial transfer timing (master mode) (during communication at different potential)**

(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number ($p = 00, 01, 10, 20, 30, 31$), m: Unit number ($m = 00, 01, 02, 10, 12, 13$), n: Channel number ($n = 0, 2$), g: PIM and POM number ($g = 0, 1, 4, 5, 8, 14$)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

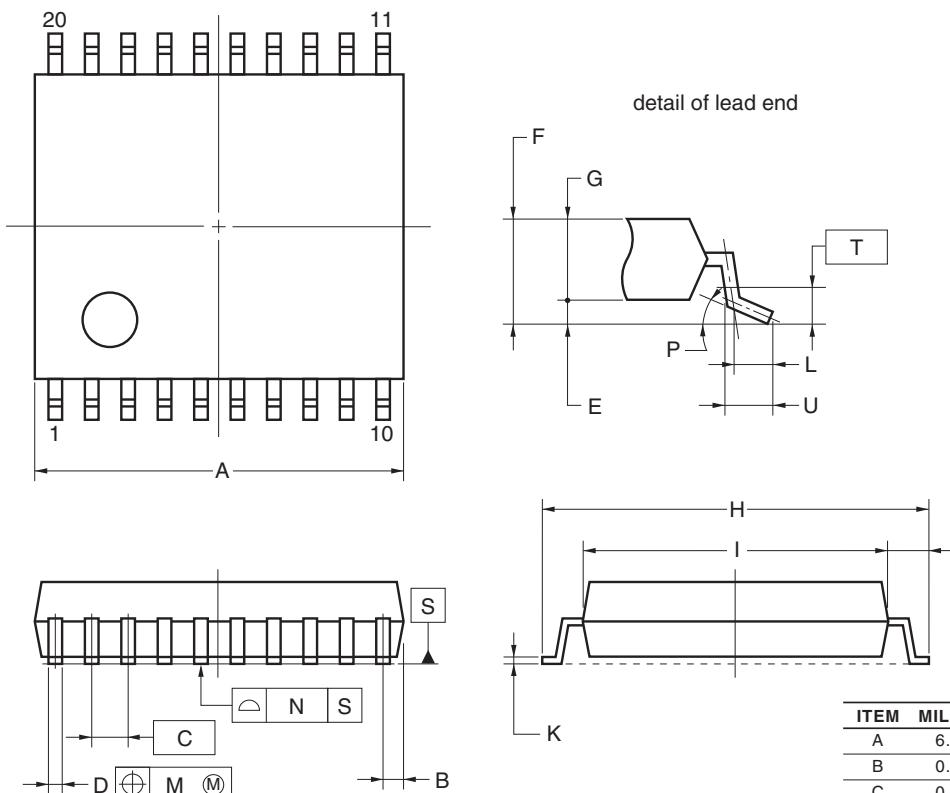
4. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

4. PACKAGE DRAWINGS

4.1 20-pin Products

R5F1006AASP, R5F1006CASP, R5F1006DASP, R5F1006EASP
 R5F1016AASP, R5F1016CASP, R5F1016DASP, R5F1016EASP
 R5F1006ADSP, R5F1006CDSP, R5F1006DDSP, R5F1006EDSP
 R5F1016ADSP, R5F1016CDSP, R5F1016DDSP, R5F1016EDSP
 R5F1006AGSP, R5F1006CGSP, R5F1006DGSP, R5F1006EGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-0300-0.65	PLSP0020JC-A	S20MC-65-5A4-3	0.12



NOTE

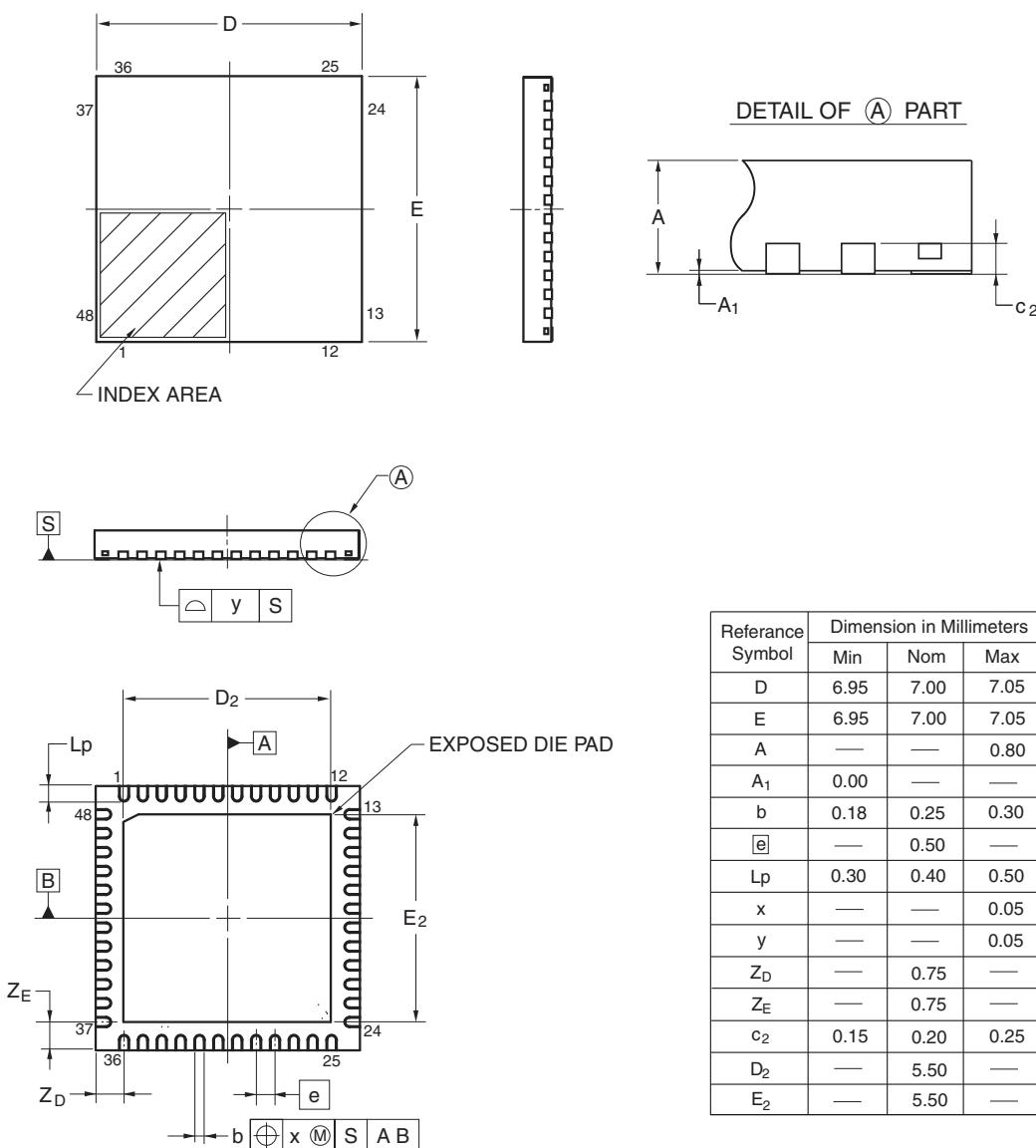
Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	6.65±0.15
B	0.475 MAX.
C	0.65 (T.P.)
D	0.24 ^{+0.08} _{-0.07}
E	0.1±0.05
F	1.3±0.1
G	1.2
H	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
P	3° ^{+5°} _{-3°}
T	0.25
U	0.6±0.15

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R5F100GAANA, R5F100GCANA, R5F100GDANA, R5F100GEANA, R5F100GFANA, R5F100GGANA,
 R5F100GHANA, R5F100GJANA, R5F100GKANA, R5F100GLANA
 R5F101GAANA, R5F101GCANA, R5F101GDANA, R5F101GEANA, R5F101GFANA, R5F101GGANA,
 R5F101GHANA, R5F101GJANA, R5F101GKANA, R5F101GLANA
 R5F100GADNA, R5F100GCDNA, R5F100GDDNA, R5F100GEDNA, R5F100GFDNA, R5F100GGDNA,
 R5F100GHDNA, R5F100GJDNA, R5F100GKDNA, R5F100GLDNA
 R5F101GADNA, R5F101GCDNA, R5F101GDDNA, R5F101GEDNA, R5F101GFDNA, R5F101GGDNA,
 R5F101GHDNA, R5F101GJDNA, R5F101GKDNA, R5F101GLDNA
 R5F100GAGNA, R5F100GCGNA, R5F100GDGNA, R5F100GEGNA, R5F100GFGNA, R5F100GGGNA,
 R5F100GHGNA, R5F100GJGNA

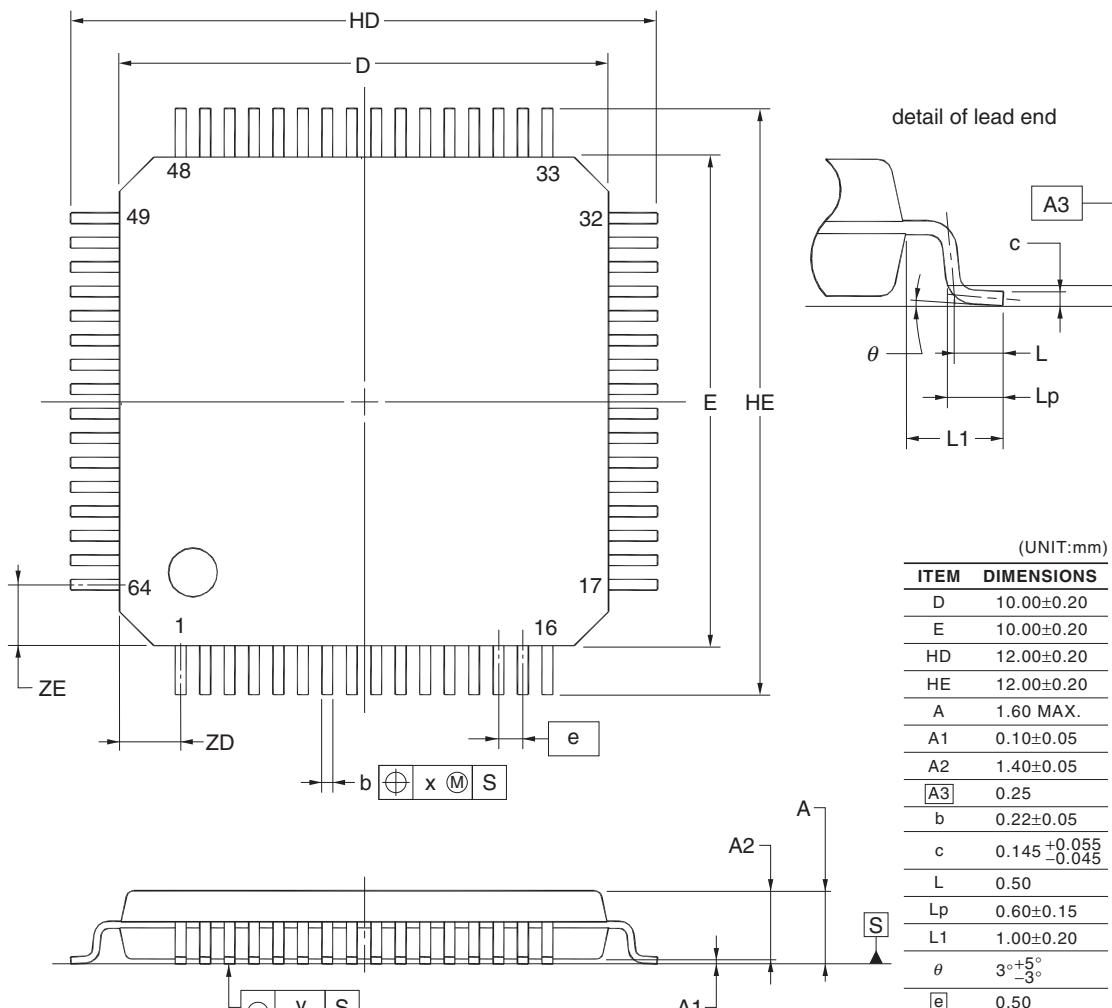
JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-HWQFN48-7x7-0.50	PWQN0048KB-A	48PQN-A P48K8-50-5B4-6	0.13



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R5F100LCAF, R5F100LDAFB, R5F100LEAFB, R5F100LFAFB, R5F100LGAFB, R5F100LHAFB, R5F100LJAFB,
 R5F100LKAFB, R5F100LLAFB
 R5F101LCAF, R5F101LDAFB, R5F101LEAFB, R5F101LFAFB, R5F101LGAFB, R5F101LHAFB,
 R5F101LJAFB, R5F101LKAFB, R5F101LLAFB
 R5F100LCDFB, R5F100LDDFB, R5F100LEDFB, R5F100LFDFB, R5F100LGDFB, R5F100LHDFB, R5F100LJDFB,
 R5F100LKDFB, R5F100LLDFB
 R5F101LCDFB, R5F101LDDFB, R5F101LEDFB, R5F101LFDFB, R5F101LGDFB, R5F101LHDFB,
 R5F101LJDFB, R5F101LKDFB, R5F101LLDFB
 R5F100LCGFB, R5F100LDGFB, R5F100LEGFB, R5F100LFGFB, R5F100LGGFB, R5F100LHGFB,
 R5F100LJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP64-10x10-0.50	PLQP0064KF-A	P64GB-50-UEU-2	0.35

**NOTE**

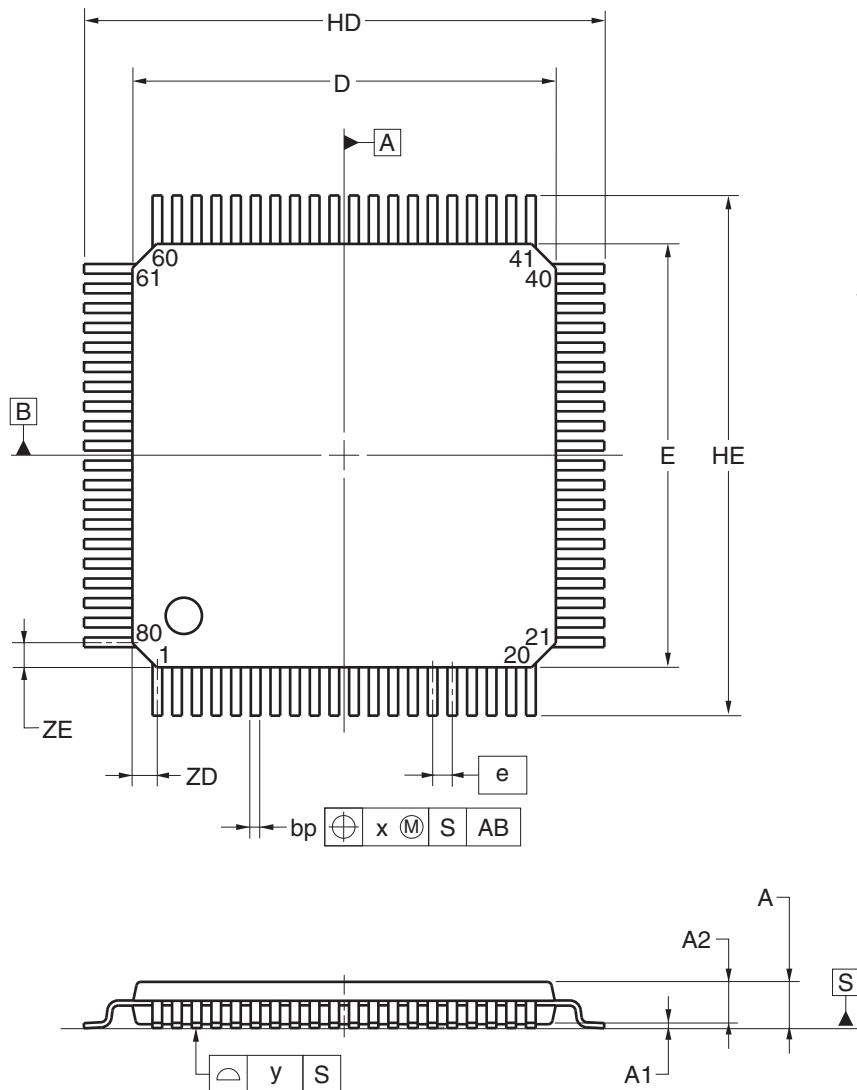
Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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4.12 80-pin Products

R5F100MFAFA, R5F100MGAFA, R5F100MHAFA, R5F100MJAFA, R5F100MKAFA, R5F100MLAFA
 R5F101MFAFA, R5F101MGAFA, R5F101MHAFA, R5F101MJAFA, R5F101MKAFA, R5F101MLAFA
 R5F100MFDFA, R5F100MGDFA, R5F100MHDFA, R5F100MJ DFA, R5F100MK DFA, R5F100ML DFA
 R5F101MFDFA, R5F101MGDFA, R5F101MHDFA, R5F101MJ DFA, R5F101MK DFA, R5F101ML DFA
 R5F100MFGFA, R5F100MGGFA, R5F100MHGFA, R5F100MJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP) [g]
P-LQFP80-14x14-0.65	PLQP0080JB-E	P80GC-65-UBT-2	0.69



Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	13.80	14.00	14.20
E	13.80	14.00	14.20
HD	17.00	17.20	17.40
HE	17.00	17.20	17.40
A	—	—	1.70
A1	0.05	0.125	0.20
A2	1.35	1.40	1.45
A3	—	0.25	—
bp	0.26	0.32	0.38
c	0.10	0.145	0.20
L	—	0.80	—
Lp	0.736	0.886	1.036
L1	1.40	1.60	1.80
θ	0°	3°	8°
e	—	0.65	—
x	—	—	0.13
y	—	—	0.10
ZD	—	0.825	—
ZE	—	0.825	—

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